

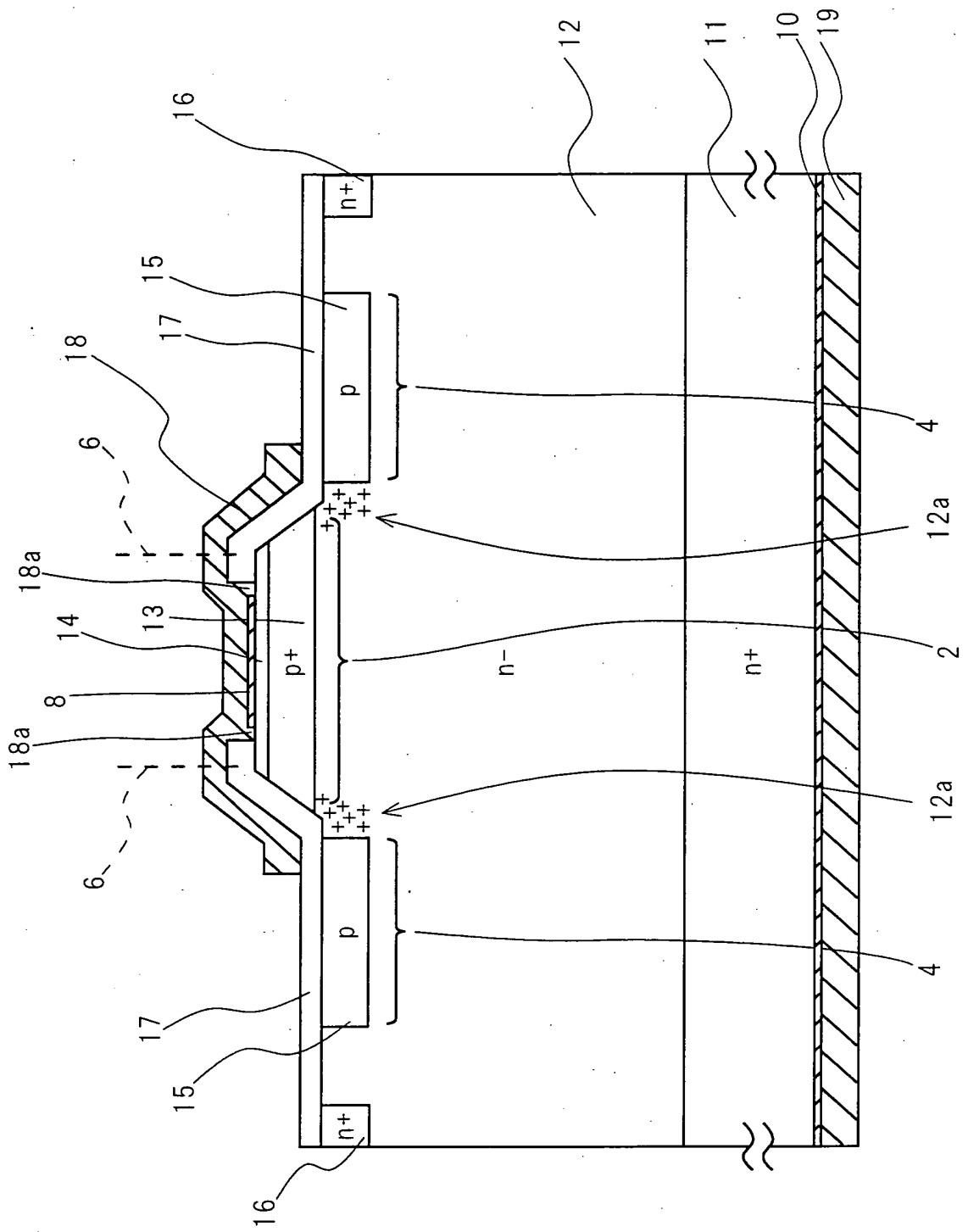
[illegible]

Fig. 2

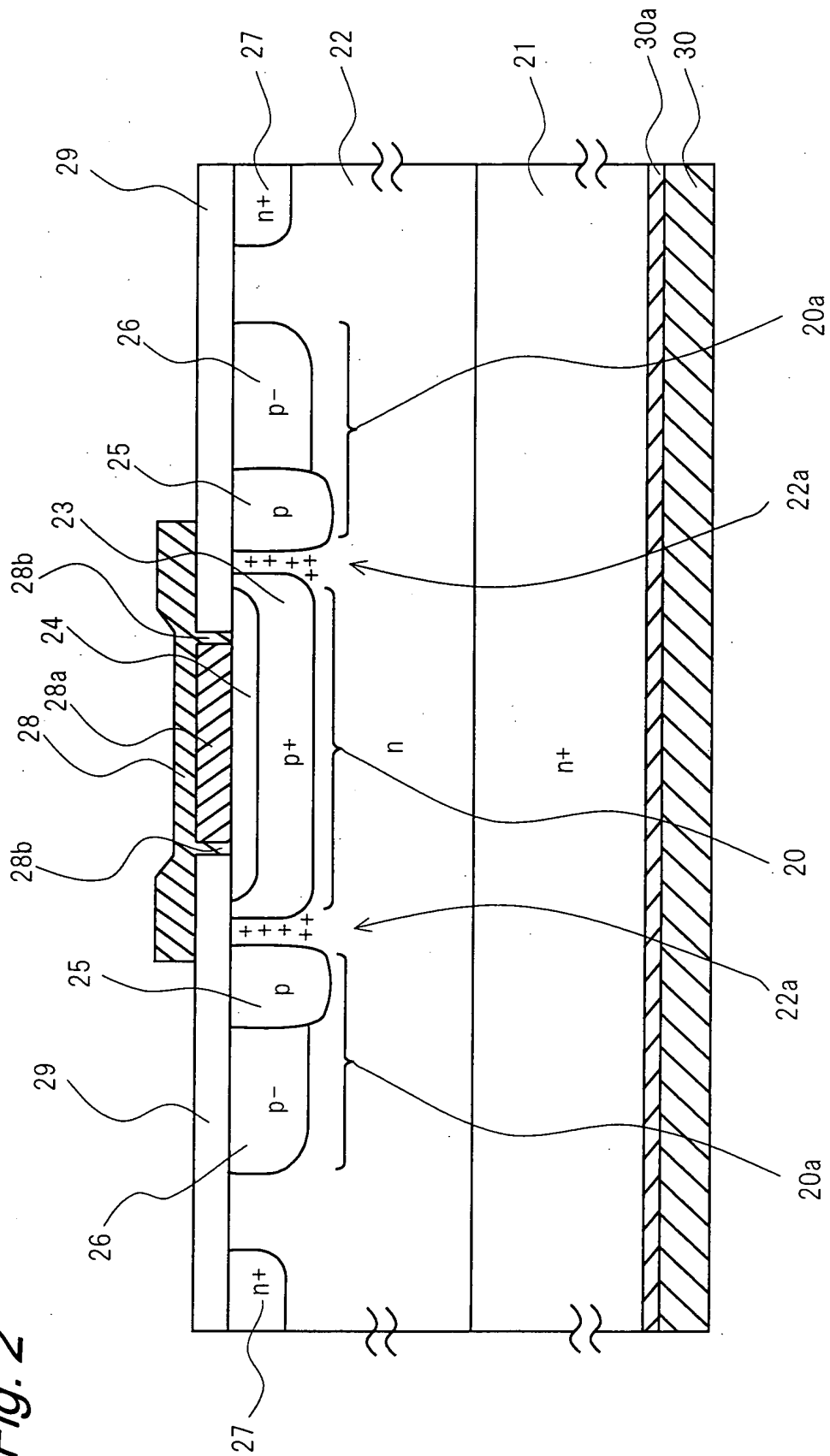


Fig. 3

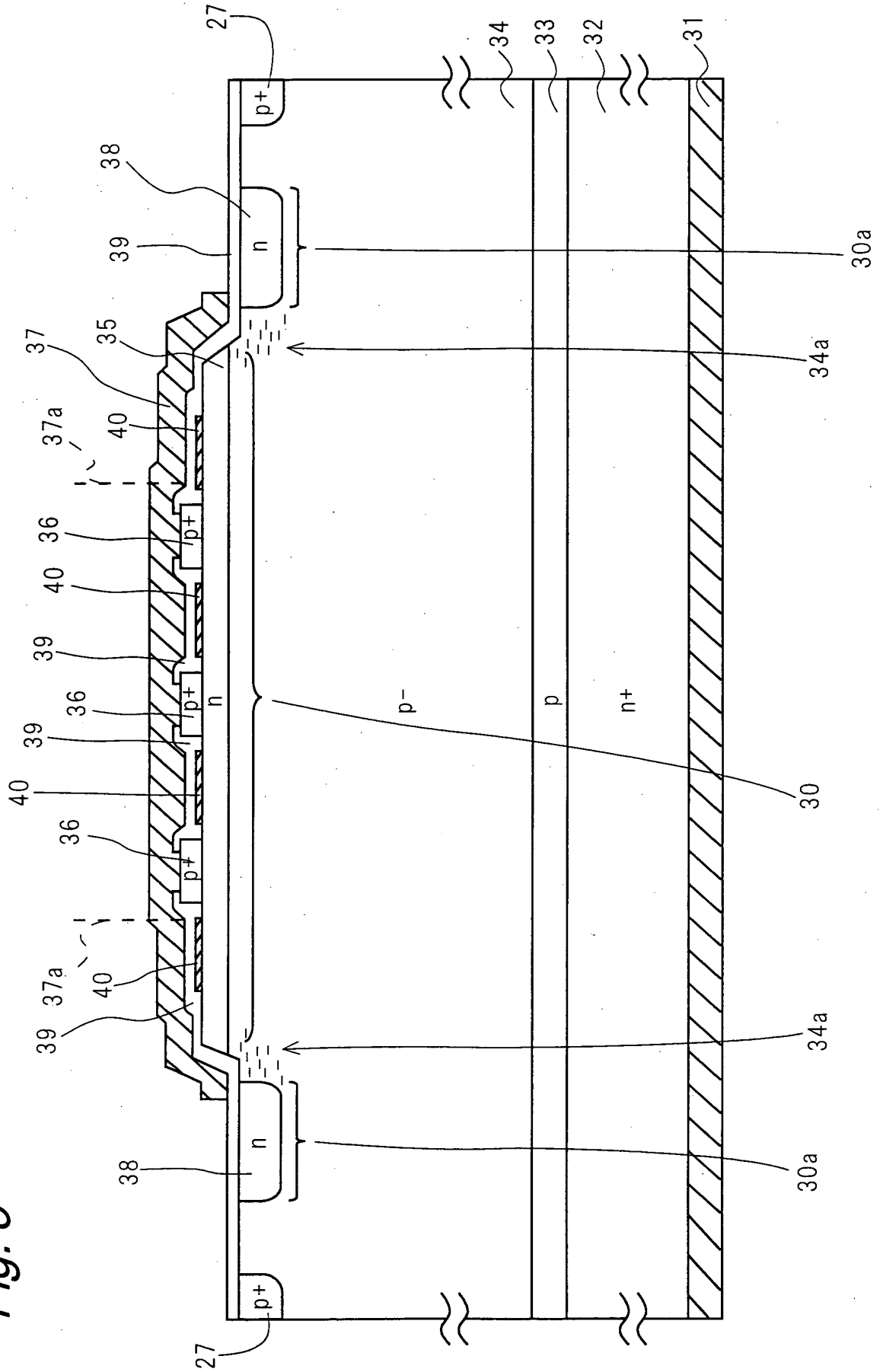


Fig. 4

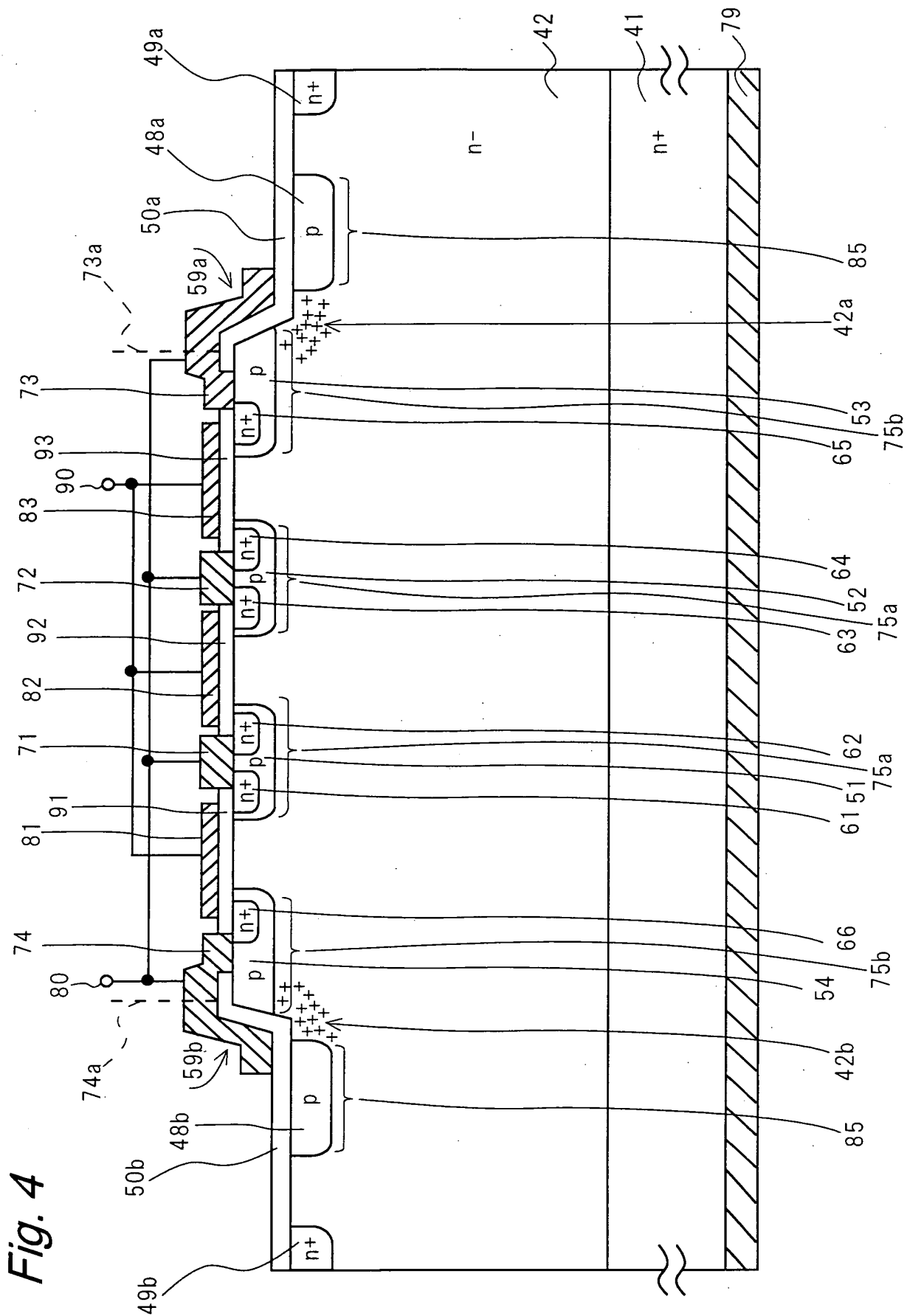
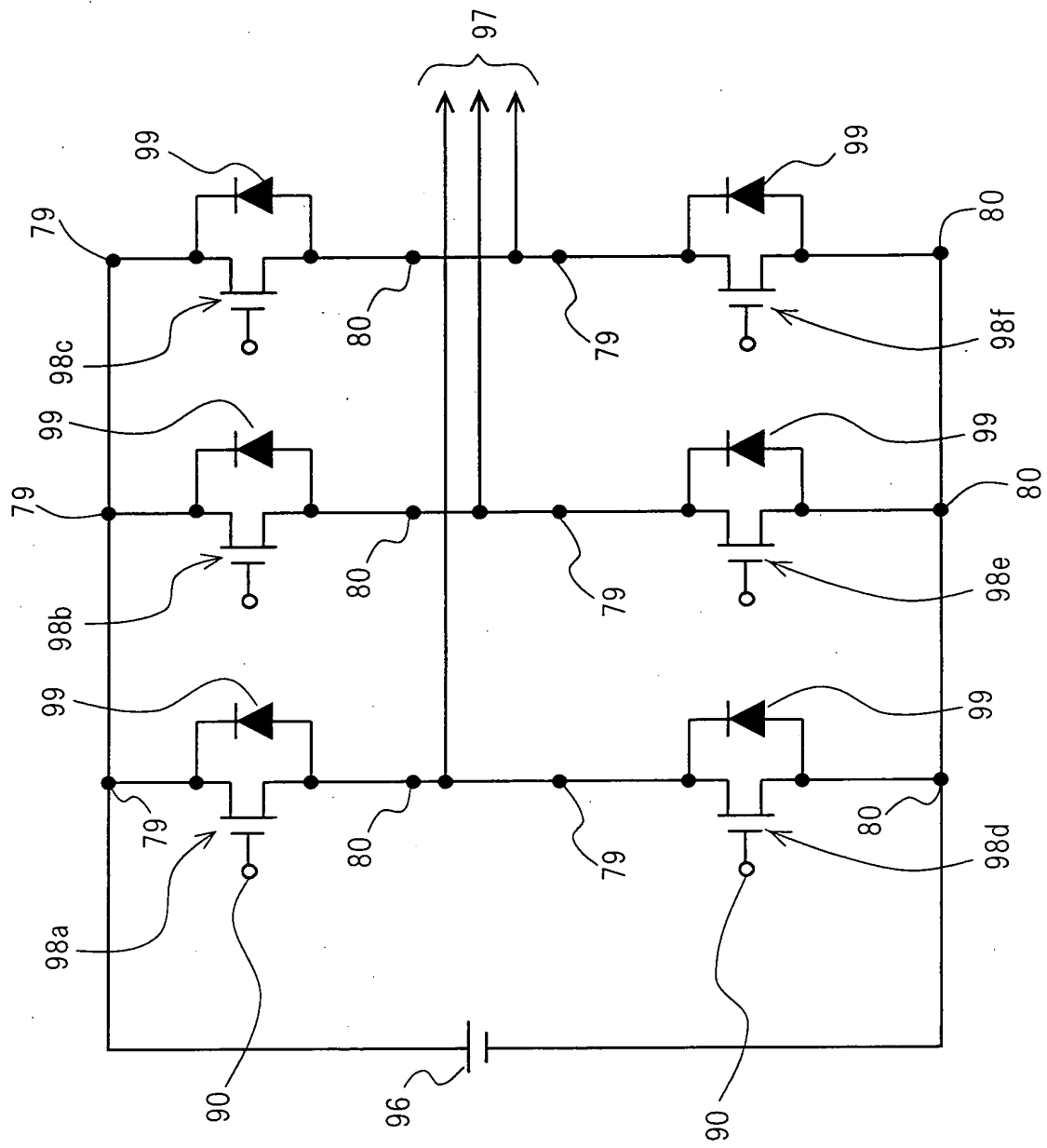


Fig. 5



This diagram shows a cross-sectional view of a semiconductor device. It features a substrate with a series of layers: a bottom layer (10), a middle layer (11), and a top layer (12). A trench (13) is formed in the top layer (12). The trench is filled with a material (14) and has a sidewall (15). The bottom of the trench is labeled with a p+ region. The top surface of the device is labeled with an n+ region. The trench is flanked by p regions (16). The device is shown in a perspective view, with a dashed line (18) indicating a cross-section. The trench is labeled with a p+ region at the bottom and a p region on the sidewall. The top surface is labeled with an n+ region. The trench is flanked by p regions (16). The device is shown in a perspective view, with a dashed line (18) indicating a cross-section.

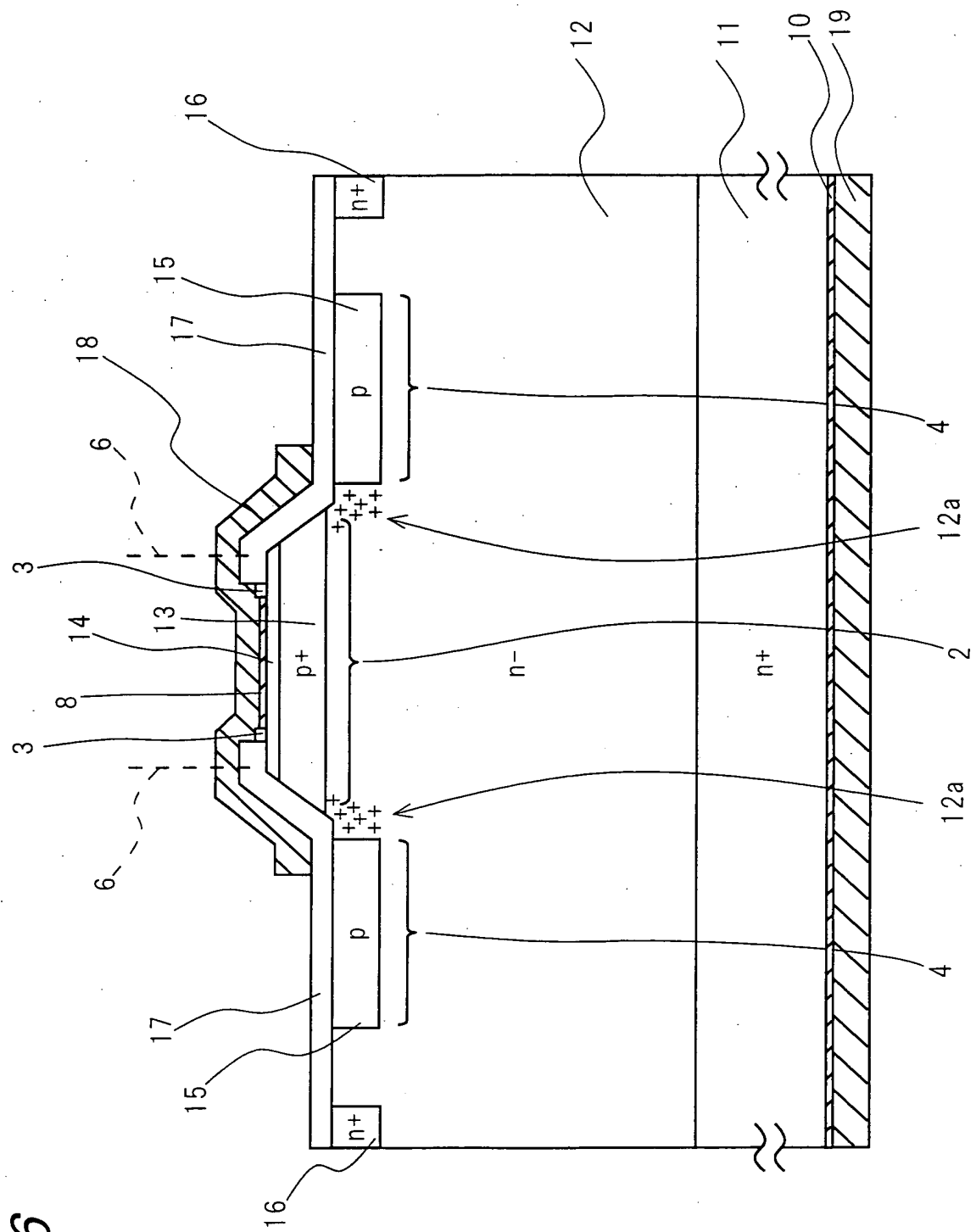


Fig. 7

